

# NTNS3A91PZ

## Small Signal MOSFET

-20 V, -223 mA, Single P-Channel,  
0.62 x 0.62 x 0.4 mm XLLGA3 Package

### Features

- Single P-Channel MOSFET
- Ultra Small and Thin Package (0.62 x 0.62 x 0.4 mm)
- Low  $R_{DS(on)}$  Solution in 0.62 x 0.62 mm Package
- 1.5 V Gate Voltage Rating
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Small Signal Load Switch
- Analog Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Products

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Units	
Drain-to-Source Voltage		$V_{DSS}$	-20	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 8.0$	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	-223	mA
				$T_A = 85^\circ\text{C}$	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	-240		
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	121	mW
				$T_A = 25^\circ\text{C}$	
Pulsed Drain Current		$t_p = 10 \mu\text{s}$	$I_{DM}$	-669	mA
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to 150		$^\circ\text{C}$
Source Current (Body Diode)		$I_S$	-121		mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260		$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	1035	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5$ s (Note 1)	$R_{\theta JA}$	895	

1. Surface Mounted on FR4 Board using the minimum recommended pad size, (or 2 mm<sup>2</sup>), 1 oz Cu.
2. Pulse Test: pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .



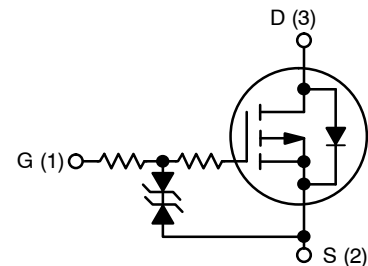
ON Semiconductor®

<http://onsemi.com>

### MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
-20 V	1.6 $\Omega$ @ -4.5 V	-223 mA
	2.4 $\Omega$ @ -2.5 V	
	3.3 $\Omega$ @ -1.8 V	
	4.5 $\Omega$ @ -1.5 V	

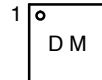
### P-Channel MOSFET



### MARKING DIAGRAM



XLLGA3  
CASE 713AB



D = Specific Device Code  
M = Date Code

### ORDERING INFORMATION

Device	Package	Shipping†
NTNS3A91PZT5G	XLLGA3 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTNS3A91PZ

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
-----------	--------	----------------	-----	-----	-----	-------

### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250\ \mu\text{A}$ , ref to $25^\circ\text{C}$		11		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = -20\text{ V}$ $T_J = 25^\circ\text{C}$			-1.0	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8.0\text{ V}$			$\pm 2.0$	$\mu\text{A}$

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$	-0.4		-1.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.1		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -100\text{ mA}$		1.1	1.6	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -50\text{ mA}$		1.5	2.4	
		$V_{GS} = -1.8\text{ V}, I_D = -20\text{ mA}$		2.0	3.3	
		$V_{GS} = -1.5\text{ V}, I_D = -10\text{ mA}$		2.5	4.5	
Forward Transconductance	$g_{FS}$	$V_{DS} = -5\text{ V}, I_D = -100\text{ mA}$		0.41		S
Source-Drain Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = -10\text{ mA}$		-0.6	-1.0	V

### CHARGES & CAPACITANCES

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 10\text{ kHz}, V_{DS} = -15\text{ V}$		41		$\text{pF}$
Output Capacitance	$C_{OSS}$			4.6		
Reverse Transfer Capacitance	$C_{RSS}$			4.1		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V}, I_D = -200\text{ mA}$		1.1		$\text{nC}$
Threshold Gate Charge	$Q_{G(TH)}$			0.1		
Gate-to-Source Charge	$Q_{GS}$			0.2		
Gate-to-Drain Charge	$Q_{GD}$			0.23		

### SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -15\text{ V}, I_D = -200\text{ mA}, R_G = 2\ \Omega$		41		$\text{ns}$
Rise Time	$t_r$			97		
Turn-Off Delay Time	$t_{d(OFF)}$			571		
Fall Time	$t_f$			286		

3. Switching characteristics are independent of operating junction temperatures.

# NTNS3A91PZ

## TYPICAL CHARACTERISTICS

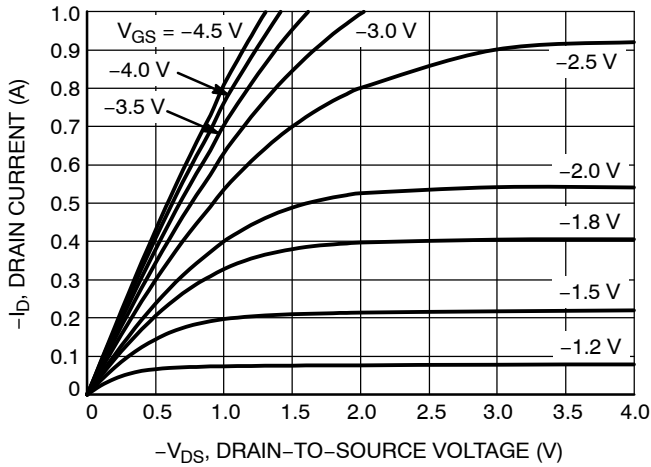


Figure 1. On-Region Characteristics

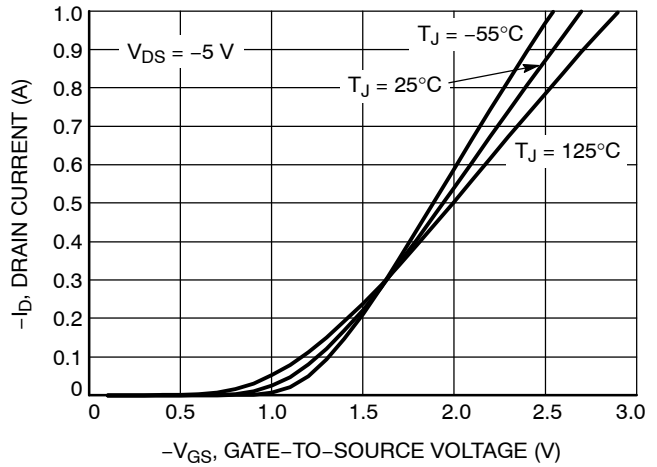


Figure 2. Transfer Characteristics

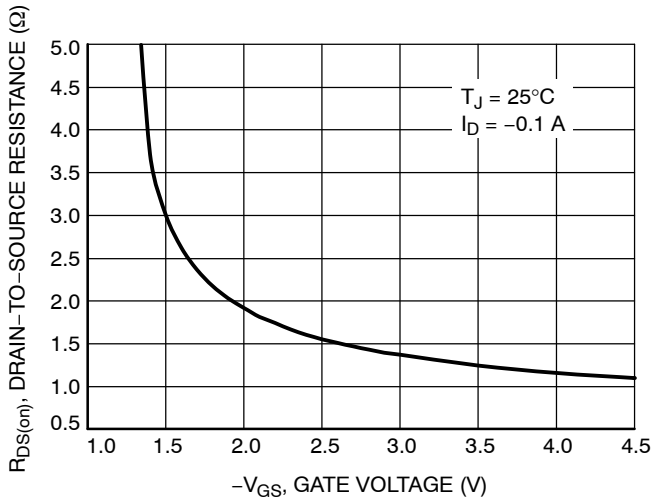


Figure 3. On-Resistance vs. Gate-to-Source Voltage

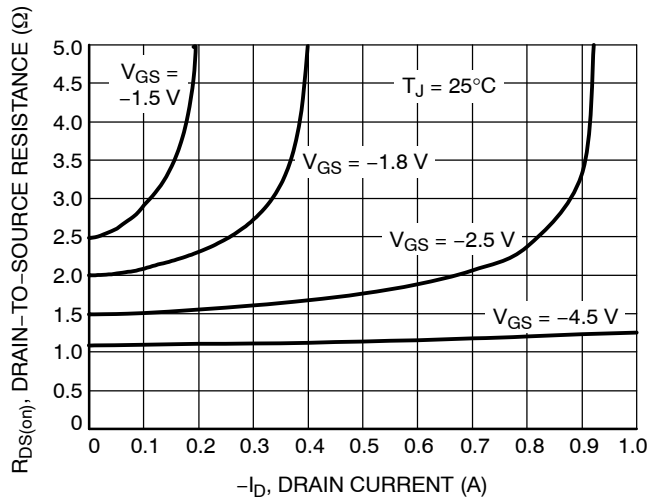


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

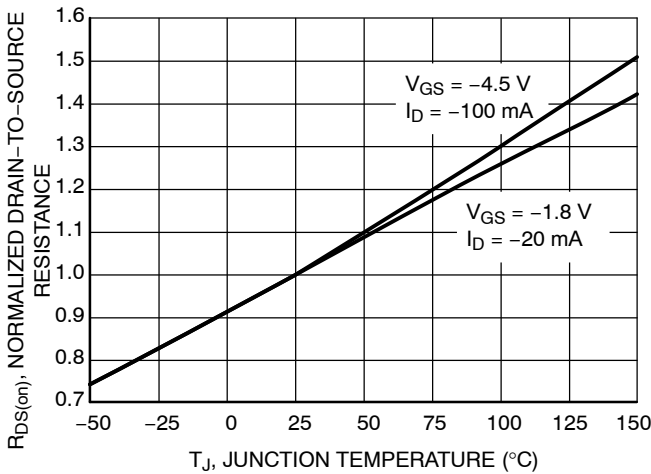


Figure 5. On Resistance Variation with Temperature

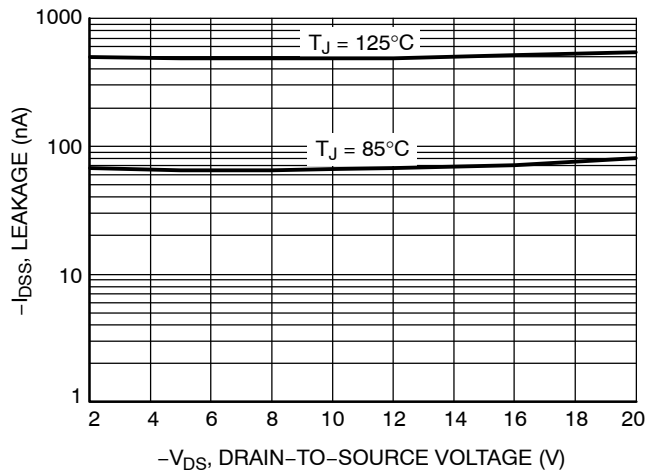


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NTNS3A91PZ

## TYPICAL CHARACTERISTICS

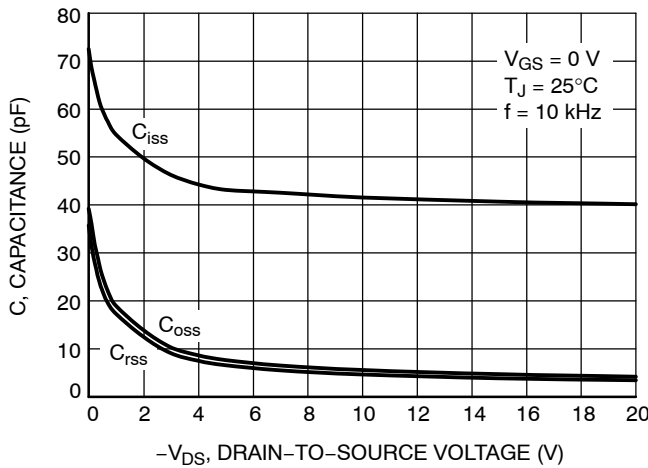


Figure 7. Capacitance Variation

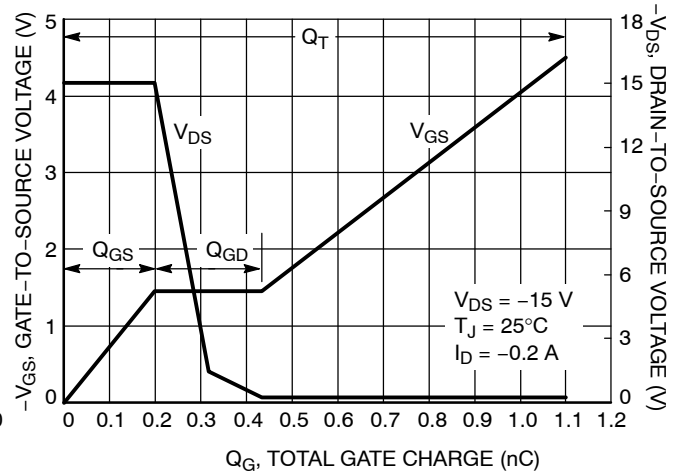


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

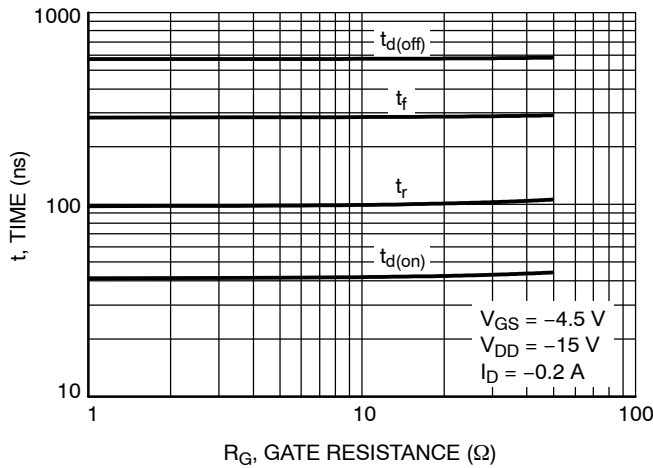


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

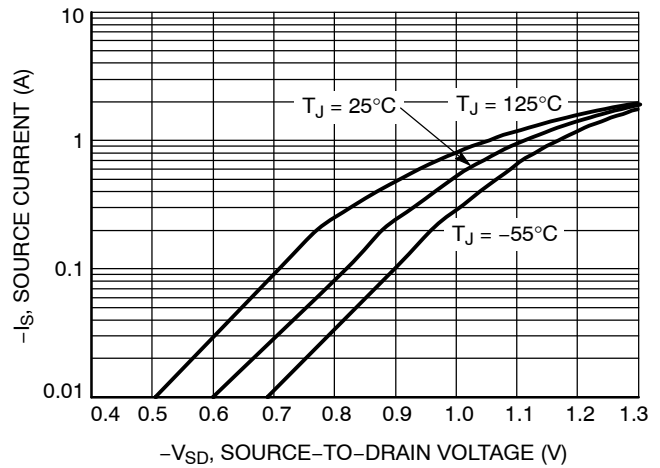


Figure 10. Diode Forward Voltage vs. Current

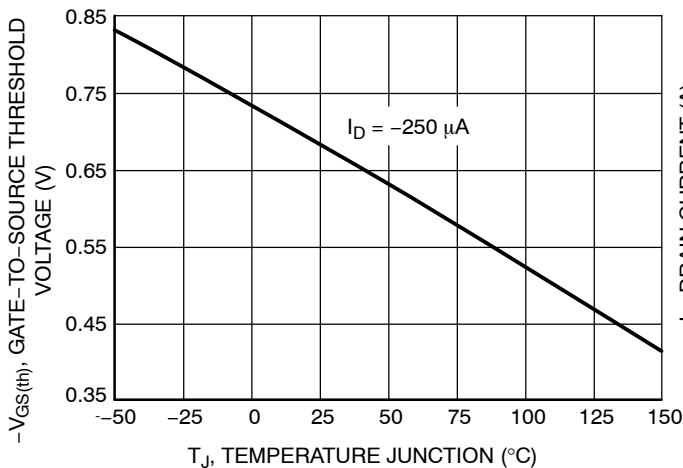


Figure 11. Threshold Voltage

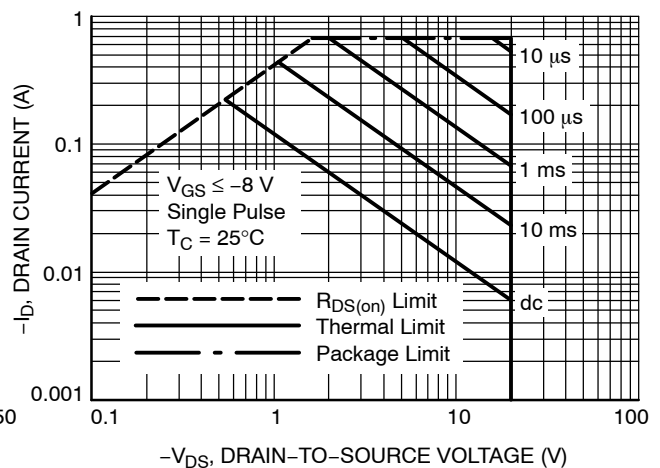


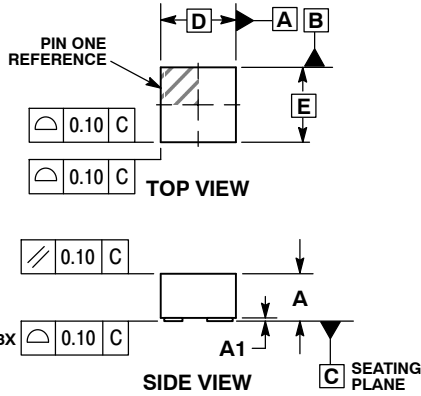
Figure 12. Maximum Rated Forward Biased Safe Operating Area



# NTNS3A91PZ

## PACKAGE DIMENSIONS

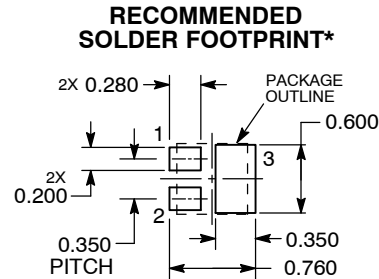
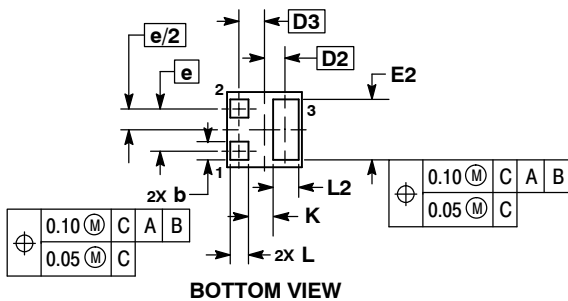
**XLLGA3, 0.62x0.62, 0.35P**  
**CASE 713AB**  
**ISSUE O**



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS		
DIM	MIN	MAX
A	0.340	0.440
A1	0.000	0.030
b	0.100	0.200
D	0.620 BSC	
D2	0.175 BSC	
D3	0.205 BSC	
E	0.620 BSC	
E2	0.400	0.600
e	0.350 BSC	
K	0.200 REF	
L	0.090	0.210
L2	0.110	0.310



DIMENSIONS: MILLIMETERS

\*Additional information concerning board mounting for this package may be found in Document AND9099/D, "Board Level Application Note for XLLGA 3-Lead 0.62x0.62 Package". For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

**LITERATURE FULFILLMENT:**  
 Literature Distribution Center for ON Semiconductor  
 P.O. Box 5163, Denver, Colorado 80217 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
 USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
 Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
 Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative

# AMEYA360

## Components Supply Platform

Authorized Distribution Brand :



Website :

Welcome to visit [www.ameya360.com](http://www.ameya360.com)

Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd  
Minhang District, Shanghai , China

➤ Sales :

Direct +86 (21) 6401-6692

Email [amall@ameya360.com](mailto:amall@ameya360.com)

QQ 800077892

Skype [ameyasales1](#) [ameyasales2](#)

➤ Customer Service :

Email [service@ameya360.com](mailto:service@ameya360.com)

➤ Partnership :

Tel +86 (21) 64016692-8333

Email [mkt@ameya360.com](mailto:mkt@ameya360.com)